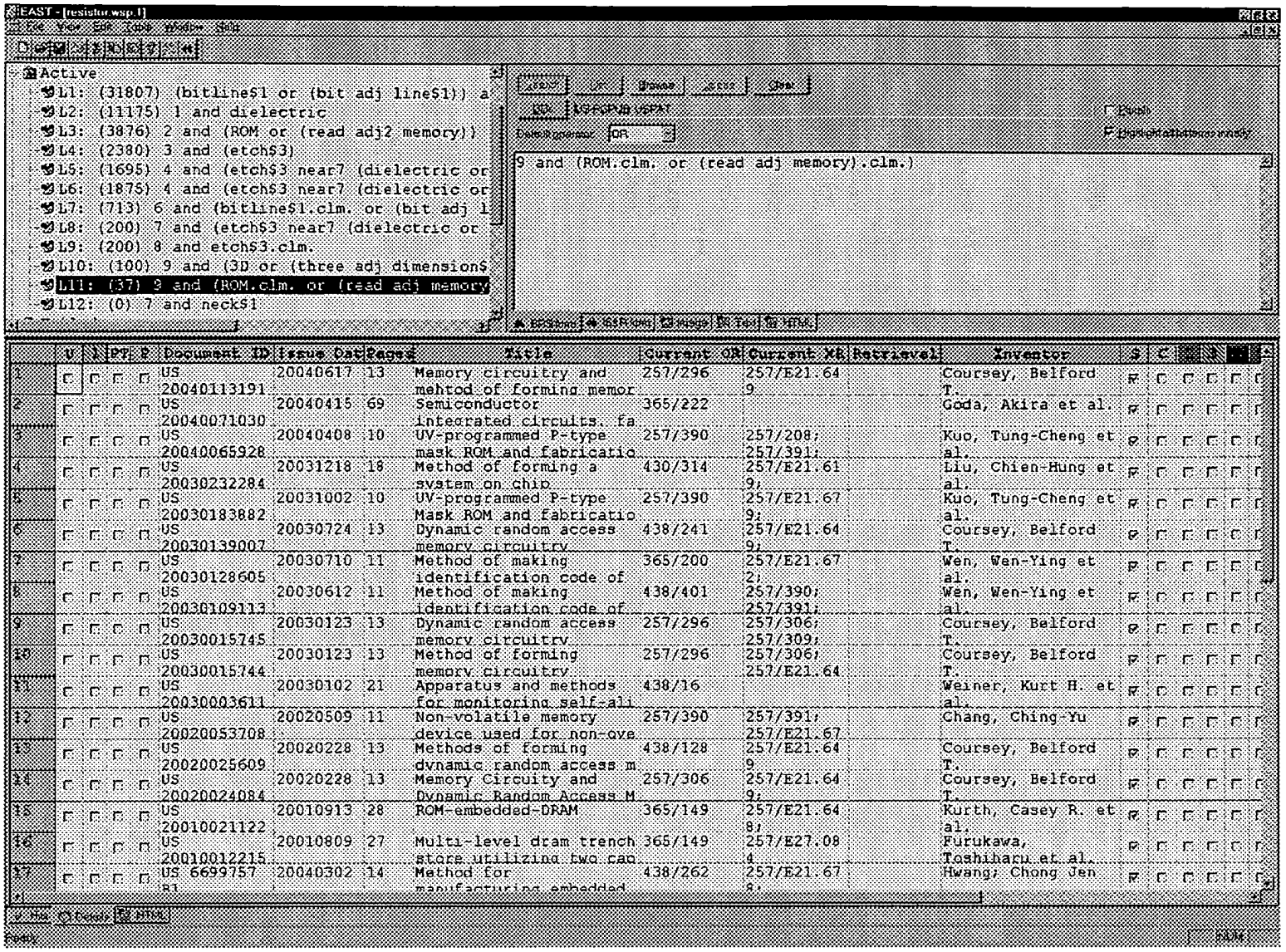

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval	Inventor	$	C	3
1	☐	☐	☐	☐	US 20040113191	20040617	13	Memory circuitry and mehtod of forming memor	257/296	257/E21.64 9		Coursey, Belford T.	☑	☐	☐
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6	☐	☐	☐	☐	US 20030139007	20030724	13	Dynamic random access memory circuitry	438/241	257/E21.64 9;		Coursey, Belford T.	☑	☐	☐
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8	☐	☐	☐	☐	US 20030109113	20030612	11	Method of making identification code of	438/401	257/390; 257/391;		Wen, Wen-Ying et al.	☑	☐	☐
9	☐	☐	☐	☐	US 20030015745	20030123	13	Dynamic random access memory circuitry	257/296	257/306; 257/309;		Coursey, Belford T.	☑	☐	☐
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14	☐	☐	☐	☐	US 20020024084	20020228	13	Memory circuitry and Dynamic Random Access M	257/306	257/E21.64 9;		Coursey, Belford T.	☑	☐	☐
15	☐	☐	☐	☐	US 20010021122	20010913	28	ROM-embedded-DRAM	365/149	257/E21.64 8;		Kurth, Casey R. et al.	☑	☐	☐
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